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| (54) Title: EXTENDED NITRIDE MATERIAL COMPRISING β -C ₃ N ₄ | | | |
| (57) Abstract | | | |
| <p>An extended nitride material comprises β-C₃N₄. A method of forming an extended nitride material includes forming an atomic nitrogen source, forming an elemental reagent source and combining the atomic nitrogen and elemental reagent to form the extended nitride material. The elemental reagent is reactive with the atomic nitrogen of the atomic nitrogen source to form the extended nitride material. The apparatus of the invention can include, for example, a radio-frequency (rf) discharge nozzle (26) for forming the atomic nitrogen source, such as an atomic nitrogen beam (24). The elemental reagent source can be formed by employing a pulsed laser to ablate a suitable target (32), such as a graphite target, to thereby form an ablation plume (38) of elemental carbon. The ablation plume (38) and the atomic nitrogen beam (24) combine and cause the elemental carbon reagent and the atomic nitrogen to react and form the extended nitride material. The extended nitride material can accumulate as a film on a suitable substrate (40), such as Si(100) or polycrystalline nickel.</p> | | | |
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INTERNATIONAL SEARCH REPORT

Int. Application No

PCT/US 94/07964

A. CLASSIFICATION F SUBJECT MATTER
IPC 6 C23C14/06 C23C14/28

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC 6 C23C

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

C. DOCUMENTS CONSIDERED TO BE RELEVANT

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| A | see table 2 | 4-9, 13-18, 21-44, 46-50 |
| X | --- PATENT ABSTRACTS OF JAPAN vol. 016, no. 469 (E-1271) 29 September 1992 & JP,A,04 167 405 (ANELVA CORP) 15 June 1992 | 20-22, 46,47 |
| Y | see abstract | 23,24, 48-50 |
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☒ Further documents are listed in the continuation of box C.☒ Patent family members are listed in annex.

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C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

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